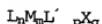


What is claimed is:

1. An organometallic precursor represented by the following Formula 1, for forming a metal film or pattern:

Formula 1



{wherein,

M is a transition metal; L' is a neutral ligand;

X is an anion that may coordinate with the transition metal;

m is an integer of 1 to 10, provided that when m is two or more, each M may or may not be the same as each other;

p is an integer of 0 to 40, and q is an integer of 0 to 10, provided that when p or q is two or higher, L' s or Xs are independently identical or different with one another, and p and q are not 0 at the same time; and

L is a hydrazine compound coordinating the transition metal, represented by the following Formula 2:

Formula 2



{wherein,

R<sub>1</sub>, R<sub>2</sub>, R<sub>3</sub> and R<sub>4</sub> are independently hydrogen, alkyl or aryl of 1 to 20 carbon atoms having substitution groups; or R<sub>5</sub>C<sup>0</sup>-, provided that the substitution groups are selected from the group consisting of halogen groups including F, Cl, Br or I, amine groups, hydroxyl groups, -SH(sulphydril) groups, cyano groups,

sulphonic acid groups ( $\text{SO}_3\text{H}$ ),  $\text{R}_6\text{S}-$ ,  $\text{R}_6\text{O}-$  ( $\text{R}_6$  is an alkyl or aryl group containing 1 to 20 carbons),  $\text{R}_6\overset{\text{O}}{\underset{\text{C}}{\text{C}}}-$ , and nitrile groups, and  $\text{R}_5$  is  $\text{R}'$ ,  $\text{R}'_2\text{N}$ , or  $\text{R}'\text{O}$  ( $\text{R}'$  is hydrogen, or an alkyl or aryl group containing 1 to 20 carbons)]; and

$n$  is an integer of 1 to 40, provided that when  $n$  is two or more,  $\text{L}_s$  are independently identical or different with one another}.

2. The organometallic precursor as set forth in Claim 1, wherein  $\text{M}$  is a metal selected from the group consisting of  $\text{Ag}$ ,  $\text{Au}$ ,  $\text{Cu}$ ,  $\text{Pd}$ ,  $\text{Pt}$ ,  $\text{Os}$ ,  $\text{Rh}$ ,  $\text{Co}$ ,  $\text{Ni}$ ,  $\text{Cd}$ ,  $\text{Ir}$ , and  $\text{Fe}$ ;  $\text{L}'$  is a ligand bonded to the metal, containing donor atoms including  $\text{N}$ ,  $\text{P}$ ,  $\text{As}$ ,  $\text{O}$ ,  $\text{S}$ ,  $\text{Se}$ , or  $\text{Te}$  and having 20 or less carbons; and  $\text{X}$  is one or more anion that can coordinate a metal atom, the anion being selected from the group consisting of  $\text{OH}^-$ ,  $\text{CN}^-$ ,  $\text{NO}_2^-$ ,  $\text{NO}_3^-$ , halide ( $\text{F}^-$ ,  $\text{Cl}^-$ ,  $\text{Br}^-$ , or  $\text{I}^-$ ), trifluoroacetate, isothiocyanate, tetraalkylborate ( $\text{BR}_4^-$ ,  $\text{R}$  is  $\text{Me}$ ,  $\text{Et}$  or  $\text{Ph}$ ), tetrahaloborate ( $\text{BX}_4^-$ ,  $\text{X}$  is  $\text{F}$  or  $\text{Br}$ ), hexafluoro phosphate ( $\text{PF}_6^-$ ), triflate ( $\text{CF}_3\text{SO}_3^-$ ), tosylate ( $\text{Ts}^-$ ), sulphate ( $\text{SO}_4^{2-}$ ), carbonate ( $\text{CO}_3^{2-}$ ), acetylacetone, trifluoroantimonate ( $\text{SbF}_6^-$ ), and an anion containing a hydrazine group.

3. The organometallic precursor as set forth in claim 1, wherein  $\text{L}'$  is selected from the group consisting of amines; alcohols; phosphines, phosphites, or phosphine oxides; arsines; thiols; carbonyl compounds; alkenes; alkynes; and arenes.

4. The organometallic precursor as set forth in Claim 1 or 2, wherein the organometallic precursor represented by the Formula 1 is  $\text{Ag}(\text{CF}_3\text{COO})\text{CH}_3\text{CONHNH}_2$ ,  $\text{Ag}(\text{CF}_3\text{COO})\text{t-butylcarbazate}$ ,  $\text{Ag}(\text{CF}_3\text{COO})\text{benzoichydrazide}$ ,  $\text{Ag}(\text{BF}_4)\text{CH}_3\text{CONHNH}_2$ ,  $\text{Ag}(\text{SbF}_6)\text{CH}_3\text{CONHNH}_2$ ,  $\text{Ag}(\text{SO}_3\text{CF}_3)\text{CH}_3\text{CONHNH}_2$ , or  $\text{Ag}(\text{NO}_3)\text{CH}_3\text{CONHNH}_2$ .

5. A composition for forming a metal film or pattern, which comprises a hydrazine compound represented by the following Formula 2 and an organometallic compound represented by the following Formula 3:

**Formula 2**

$\text{R}_1\text{R}_2\text{NNR}_3\text{R}_4$

{wherein,

$\text{R}_1$ ,  $\text{R}_2$ ,  $\text{R}_3$  and  $\text{R}_4$  are independently hydrogen; alkyl or aryl of 1 to 20 carbon atoms having substitution groups; or  $\text{R}_5\overset{\text{O}}{\text{C}}\text{--}$ , provided that the substitution groups are selected from the group consisting of halogen groups including F, Cl, Br or I, amine groups, hydroxyl groups,  $-\text{SH}(\text{sulphydryl})$  groups, cyano groups, sulphonic acid groups ( $\text{SO}_3\text{H}$ ),  $\text{R}_6\text{S}^-$ ,  $\text{R}_6\text{O}^-$  ( $\text{R}_6$  is an alkyl or aryl group containing 1 to 20 carbons),  $\text{R}_5\overset{\text{O}}{\text{C}}\text{--}$ , and nitrile groups, and  $\text{R}_5$  is  $\text{R}'\text{N}$ , or  $\text{R}'\text{O}$  ( $\text{R}'$  is hydrogen, or an alkyl or aryl group containing 1 to 20 carbons}); and,

**Formula 3**

$\text{M}_m\text{L}'\text{--pX}_q$

{wherein,

M is a transition metal; L' is a neutral ligand;  
X is an anion that can coordinate the transition metal;  
m is an integer of one to ten, provided that when m is two or more, each M may or may not be same as each other; and  
p is an integer of 0 to 40, and q is an integer of 0 to 10, provided that when p or q is two or higher, L' s or Xs are independently identical or different with one another, and p and q are not 0 at the same time}.

6. A method of forming a metal film or pattern using a solution of the organometallic precursor of claim 1 or the composition of claim 5 with heat treatment.

7. The method as set forth in claim 6, wherein forming the metal film or pattern is performed by i) producing a pattern through a microcontact printing, a micro molding in capillary (MIMIC), an imprinting, an ink-jet printing, or a silk-screen, and ii) heating the pattern.

8. The method as set forth in claim 6, wherein the solution of organometallic precursor of claim 1 or the composition of claim 5 is prepared by dissolving the organometallic precursor or the composition in a solvent selected from the group consisting of nitriles including acetonitrile, propionitrile, pentanenitrile, hexanenitrile, heptanenitrile, and isobutynitrile; aliphatic hydrocarbons including hexane, heptane, octane, and dodecane; aromatic hydrocarbons including anisole, mesitylene, and xylene; ketones including methyl

isobutyl ketone, 1-methyl-2-pyrrolidinone, cyclohexanone, and acetone; ethers including tetrahydrofuran, diisobutyl ether, and isopropyl ether; acetates including ethyl acetate, butyl acetate, and propylene glycol methyl ether acetate; alcohols including isopropyl alcohol, butyl alcohol, hexyl alcohol, and octyl alcohol; inorganic solvents; and a mixture thereof.

9. The method as set forth in claim 6, wherein the method comprises the steps of i) dissolving the organometallic precursor of claim 1 or the composition of claim 5 in a first solvent to produce a solution and coating the solution on a substrate; ii) partially heat-treating the solution coated on the substrate at 400°C or lower; and iii) developing a heat-treated coating with a solvent to obtain the pattern.

10. The method as set forth in claim 9, wherein ii) the partial heat-treatment is conducted by using a laser beam or an electronic beam.

11. The method as set forth in claim 6, wherein the method comprises i) preparing a mold or a stamp with a fine pattern and ii) injecting or coating the organometallic precursor of claim 1 or the composition of claim 5 into the mold or on the stamp, transferring the organometallic precursor or composition onto a predetermined substrate, and heat-treating the transferred organometallic precursor or composition.